Matthias Bauer

List of Publications by Year
in descending order

12 papers	297 citations	1163117 8 h-index	1372567 10 g-index
12 all docs	12 docs citations	12 times ranked	167 citing authors

#	Article	IF	Citations
1	Group IV Materials. Series in Optics and Optoelectronics, 2013, , 1-54.	0.0	0
2	Selective Epitaxial Growth (SEG) of Highly Doped Si:P on Source/Drain Areas of NMOS Devices Using Si3H8/PH3/Cl2 Chemistry. ECS Meeting Abstracts, 2010, , .	0.0	0
3	(Invited) Selective Epitaxial Growth (SEG) of Highly Doped Si:P on Source/Drain Areas of NMOS Devices Using Si₃H₈/PH₃/Cl₂ Chemistry. ECS Transactions, 2010, 33, 629-636.	0.5	14
4	Strained n-Channel FinFETs Featuring In Situ Doped Siliconâ€"Carbon $(hbox{Si}_{1 - y}hbox{C}_{y})$ Source and Drain Stressors With High Carbon Content. IEEE Transactions on Electron Devices, 2008, 55, 2475-2483.	3.0	37
5	Siliconâ€"Carbon Stressors With High Substitutional Carbon Concentration and In Situ Doping Formed in Source/Drain Extensions of n-Channel Transistors. IEEE Electron Device Letters, 2008, 29, 460-463.	3.9	14
6	Strain Enhanced nMOS Using <i>In Situ</i> Doped Embedded $hbox{Si}_{1 - x}hbox{C}_{x}$ S/D Stressors With up to 1.5% Substitutional Carbon Content Grown Using a Novel Deposition Process. IEEE Electron Device Letters, 2008, 29, 1206-1208.	3.9	29
7	Throughput Considerations for In-Situ Doped Embedded Silicon Carbon Stressor Selectively Grown into Recessed Source Drain Areas of NMOS Devices. ECS Transactions, 2008, 13, 287-298.	0.5	8
8	Highly tensile strained siliconâ€"carbon alloys epitaxially grown into recessed source drain areas of NMOS devices. Semiconductor Science and Technology, 2007, 22, S183-S187.	2.0	53
9	Defect Free Embedded Silicon Carbon Stressor Selectively Grown into Recessed Source Drain Areas of NMOS Devices. ECS Transactions, 2007, 6, 419-427.	0.5	8
10	Tensile Strained Selective Silicon Carbon Alloys for Recessed Source Drain Areas of Devices. ECS Transactions, 2006, 3, 187-196.	0.5	21
11	Coalescence of germanium islands on silicon. Thin Solid Films, 1998, 336, 109-111.	1.8	10
12	New virtual substrate concept for vertical MOS transistors. Thin Solid Films, 1998, 336, 319-322.	1.8	103